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OTHER DOCUMENTS (Including Author (in CAPS), Title, Publication Date, Pages, etc.)

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Form PTO-1449 US Dept. of Commerce PATENT & TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	ATTY DOCKET NO. D/A0577Q1	APPLICATION NO. 09/998,334
	APPLICANT Romano et al.	
	FILING DATE 12-3-01	GROUP ART UNIT 2879

U.S. PATENT DOCUMENTS					
EXAMINER INITIAL	DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE	CLASS	SUB CLASS
JWM	3,805,601	4/23/74	Jeffers	73	88.5
CKW	3,922,475	11/25/75	Manasevit	428	539
JJ	5,394,006	2/28/95	Lin	257	506
DM	5,684,319	11/4/97	Hebert	257	336
SLO	5,825,122	10/20/98	Givargizov	313	336
CB	6,165,808	12/26/00	Zhang	438	20

## FOREIGN PATENT DOCUMENTS

	COUNTRY	DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	TRANSLATION Y/N

## OTHER DOCUMENTS (Including Author (in CAPS), Title, Publication Date, Pages, etc.)

J. S.	C. YOUTSEY, L.T. ROMANO, I. ADESIDA, "Gallium Nitride Whiskers Formed by Selective Photoenhanced Wet Etching of Dislocations," <u>Applied Physics Letters</u> , Vol. 73, No. 6, 10 August 1998, pp.797-799
J. S.	T. KOZAWA, M. SUZUKI, V. TAGA, Y. GOTOH, J. ISHIKAWA, "Fabrication of GaN Field Emitter Arrays by Selective Area Growth Technique," <u>J. Vac. Sci. Technol. B</u> 16(2), Mar/Apr. 1998, pp.833-835
EXAMINER <i>[Signature]</i> DATE CONSIDERED 4/28/03	
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	